Peregrine
Semiconductor

2015-2016
High Performance Analog
Product Catalog

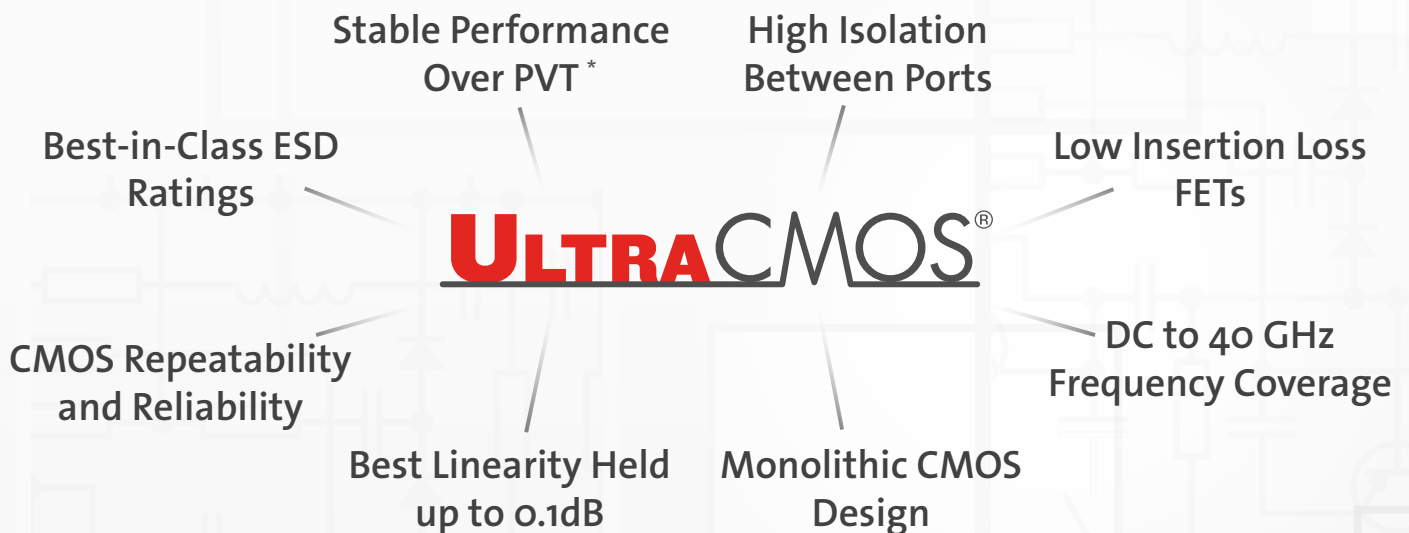# Welcome to
Peregrine Semiconductor

Peregrine Semiconductor Corporation, a Murata company, is the founder of RF silicon on insulator (SOI) and is a leading fabless provider of high-performance, integrated RF solutions. Since 1988 Peregrine and its founding team have been perfecting UltraCMOS® technology—a patented, advanced form of SOI—to deliver the performance edge needed to solve the RF market's biggest challenges, such as linearity. With products that deliver best-in-class performance and monolithic integration, Peregrine is the trusted choice for market leaders in automotive, broadband, industrial, Internet of Things, mobile devices, smartphones, space, test-and-measurement equipment and wireless infrastructure. A Murata company since December 2014, Peregrine holds more than 180 filed and pending patents and has shipped over 2 billion UltraCMOS units.

From its roots in government research-and-development innovation, Peregrine continues to revolutionize the industry with high-performance, integrated RF solutions.

Core Technology Benefits

UltraCMOS solutions provide high-performance RF, mixed-signal, passive elements and digital functions on a single device.

Stable Performance Over PVT *

High Isolation Between Ports

Best-in-Class ESD Ratings

Low Insertion Loss FETs

ULTRACMOS®

CMOS Repeatability and Reliability

DC to 40 GHz Frequency Coverage

Best Linearity Held up to 0.1dB

Monolithic CMOS Design

* PVT = Process, Voltage & Temperature

Intelligent Integration

ULTRACMOS®

Intelligent integration showcases Peregrine's ability to integrate RF, digital and analog components onto a single die. While integration has traditionally offered high-volume markets the benefit of lower cost, Peregrine uses intelligent integration to offer performance advantages such as configurability, flexibility, reliability, repeatability, ease-of-use and a reduced form factor.
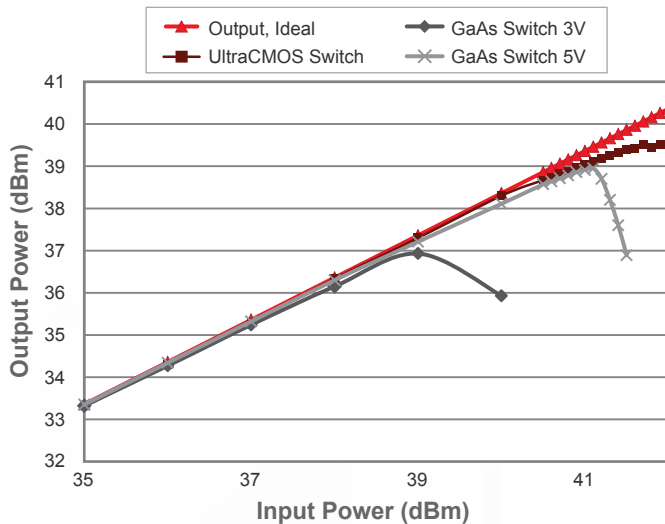
High-performance
RF Products

RF complexity is growing exponentially as more wireless devices compete for signals throughout more frequency bands, and Peregrine continues to achieve several SOI industry firsts that offer RF engineers the widest range of high-performance RF choices. UltraCMOS products allow engineers the flexibility to prioritize attributes—like small form factor, low power consumption, high reliability, radiation-hardened, high ESD ratings, programmability, affordability, reduced board area—based on use case.

Linearity Figure of Merit: P0.1dB

An UltraCMOS switch exhibits close to ideal linearity behavior up to the input 0.1dB compression point (P0.1dB), which remains invariant over power supply voltages.

Output Power (dBm) vs Input Power (dBm)

Output, Ideal	GaAs Switch 3V
UltraCMOS Switch	GaAs Switch 5V

UltraCMOS switches do not compress in the same manner as switches on other technology processes and a traditional P1dB measurement cannot be performed. Because UltraCMOS switch linearity is defined by the power handling capabilities of each switch, the P0.1dB compression point (derived from P_{MAX}) is used as the figure of merit to reflect each switch's true linearity performance.

Industry-leading Linearity Performance

PE42722 second and third harmonics (P_{IN} = 65 dBmV)

Harmonics (dBc) vs Frequency (MHz)

2fo, typ.	3fo, typ.
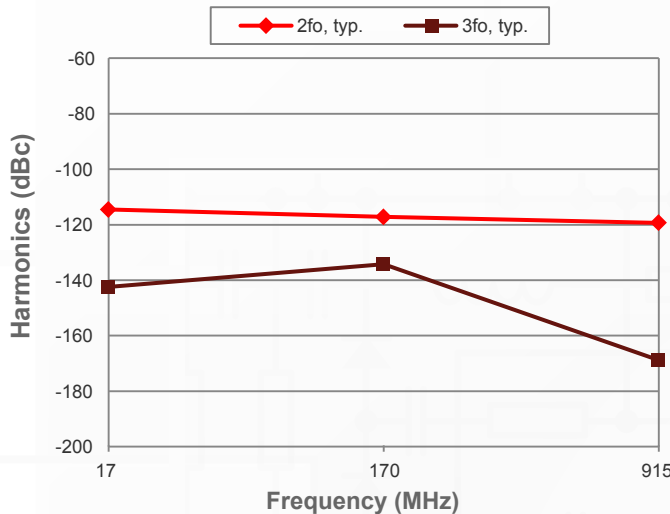
The PE42722 SPDT RF switch for DOCSIS 3.1 features unmatched linearity performance enabled by UltraCMOS, the only technology capable of addressing the linearity challenges of the future.

General-purpose RF Switches

Peregrine's broadband and general-purpose RF switches deliver an industry-leading combination of insertion loss, isolation, linearity and settling time, while routing RF signals to their respective transmit or receive paths.

Product Description[1]	Part Number	Product Highlight	Operating Frequency (MHz) Min	Operating Frequency (MHz) Max	Linearity IIP3/IIP2 (dBm)	P0.1dB (dBm)	Insertion Loss (dB) Min	Insertion Loss (dB) Max	Isolation (dB) Min	Isolation (dB) Max	V_{DD} Range (V)	ESD HBM (V)	Package
SPST, A	PE4246	Low Insertion Loss	1	5000	53 / –	33	0.8	1.3	44	55	2.7–3.3	200	6L 3×3 DFN
SPDT, A	PE4251	Low Insertion Loss	10	3000	59 / –	30.5	0.55	0.75	43	62	3.0–3.6	4000	8L MSOP
SPDT, A	PE4257	High Isolation	5	3000	55 / 80	31	0.75	1.2	44	64	2.7–3.3	1000	20L 4×4 QFN
NEW SPDT, A & R	PE42020	True DC	0 Hz	8000	62 / 115	38	0.6	1.1	34	48	11–15[4]	1000	20L 4×4 QFN
SPDT, A	PE42420[2]	High Isolation	100	6000	65 / 110	33	0.95	1.6	50	69	2.7–5.5	4000	20L 4×4 LGA
SPDT, A	PE42520	Broadband	0.009	13000	66 / 120	39	0.6	2.0	18	90	2.3–5.5	4000	16L 3×3 QFN
SPDT, A	PE42521	Broadband, FS[3]	0.009	13000	65 / 120	38	0.6	1.85	17	90	2.3–5.5	3000	16L 3×3 QFN
NEW SPDT, A	PE42522	Broadband	0.009	26500	59 / 121	33	0.7	5.3	22	73	2.3–5.5	3500	29L 4×4 LGA
NEW SPDT, A	PE42523	Broadband, FS[3]	0.009	26500	59 / 125	33	0.75	5.7	22	75	2.3–5.5	2500	29L 4×4 LGA
NEW SPDT, A	PE42553	Broadband	0.009	8000	66 / 120	39	0.6	0.85	41	90	2.3–5.5	4000	16L 3×3 QFN
SPDT, R	PE4239	Low Insertion Loss	10	3000	45 / –	27	0.7	0.9	23	32	2.7–3.3	1500	6L SC70
SPDT, R	PE4245	Low Insertion Loss	10	4000	45 / –	27	0.6	0.7	32	42	2.7–3.3	1500	6L 3×3 DFN
SPDT, R	PE4250	Low Insertion Loss	10	3000	59 / –	30.5	0.6	0.75	40	51	3.0–3.6	4000	8L MSOP
SPDT, R	PE4259	Low Insertion Loss	10	3000	55 / –	34	0.35	0.5	20	30	1.8–3.3	2000	6L SC70
NEW SPDT, R	PE423422[2]	Automotive	100	6000	73.5 / 115	34	0.25	0.9	16	41	2.3–5.5	1000	12L 2×2 QFN
SPDT, R	PE42359[2]	Automotive	10	3000	55 / –	33.5	0.35	1.1	14	35	1.8–3.3	2000	6L SC70
SPDT, R	PE42421	Low Insertion Loss	10	3000	55 / –	30.5	0.35	0.5	20	30	1.8–3.3	2000	6L SC70
SPDT, R	PE42422	Low Insertion Loss	5	6000	70 / 115	34	0.23	0.9	17	68	2.3–5.5	4000	12L 2×2 QFN
SPDT, A	PE42423	High Isolation	100	6000	65 / 120	39.5	0.8	0.95	41	51	2.3–5.5	3000	16L 3×3 QFN
SPDT, R	PE42424[2]	High Isolation, FS[3]	100	6000	61 / 125	41	0.8	0.95	34	47	2.3–5.5	2500	6L 1.5×1.5 DFN
NEW SPDT, R	PE42524	Wideband	10	40000	50 / –	32.5	0.6	5.5	33	84	–	2000	Flip Chip
SPDT, R	PE42551	Broadband	0.009	6000	50 / –	34	0.55	0.9	21	29	2.5–3.0	500	20L 4×4 QFN
SPDT, R	PE42820	High Power	30	2700	85 / –	45.5	0.3	0.7	24	35	2.3–5.5	1500	32L 5×5 QFN
SPDT, R	PE42821	High Power, FS[3]	100	2700	82 / –	45.5	0.4	0.8	24	35	2.3–5.5	1500	32L 5×5 QFN
SP3T, R	PE42430	Low Insertion Loss	100	3000	66 / 100	30	0.45	0.55	30	40	3.0–5.5	4500	8L 1.5×1.5 DFN
SP4T, A	PE42441	Low Insertion Loss	10	8000	58 / 110	31	0.8	1.2	31	45	3.0–3.55	2000	32L 5×5 LGA
SP4T, A	PE42442[2]	High Isolation	30	6000	58 / 97	35	0.9	1.9	32	61	2.3–5.5	2000	24L 4×4 QFN
SP4T, A	PE42540	Broadband	0.00001	8000	58 / 100	33	0.7	1.2	31	84	3.0–3.6	1000	32L 5×5 LGA
NEW SP4T, A	PE42542	Broadband	0.009	18000	58 / 118	33	0.7	3.1	27	90	2.3–5.5	3500	29L 4×4 LGA
NEW SP4T, A	PE42543	Broadband, FS[3]	0.009	18000	59 / 113	33	0.7	3.2	29	90	2.3–5.5	2500	29L 4×4 LGA
NEW SP4T, R	PE423641[2]	Automotive	50	3000	68 / 115	37	0.5	0.95	22	32	2.65–3.3	2000	16L 3×3 QFN
SP4T, R	PE42440	Low Insertion Loss	50	3000	67 / 96	41.5	0.45	0.85	22	34	2.7–3.3	2000	16L 3×3 QFN
SP4T, R	PE42641	Low Insertion Loss	100	3000	–	–	0.45	0.55	27.5	35	2.65–2.85	2000	16L 3×3 QFN
SP5T, A	PE42451	High Isolation	450	4000	58 / 95	35	1.6	2.25	50	68	2.7–3.3	3500	24L 4×4 QFN
SP5T, A	PE42452[2]	High Isolation	450	4000	57 / 96	35	0.95	1.6	44	61	2.3–5.5	3500	24L 4×4 QFN
SP(3/5)T, R	PE42850	High Power	30	1000	42 / –	45.5	0.25	0.35	30	36	2.3–5.5	1500	32L 5×5 QFN
SP(3/5)T, R	PE42851	High Power, FS[3]	100	1000	42 / –	45.5	0.25	0.4	30	36	2.3–5.5	1500	32L 5×5 QFN

Note 1: Absorptive (A) or Reflective (R).
Note 2: Operating temperature up to +105 °C.
Note 3: Fast switching.

Note 4: Requires external negative voltage (V_{SS}, –11V to –15V) for operation. See datasheet for details.

75Ω / 50Ω

Our general-purpose reflective 50Ω switches can also be used in a 75Ω environment.

TE / ATE Switches

Peregrine offers complementary devices for test equipment (TE) and automated test equipment (ATE) applications. HaRP™ technology enhancements reduce gate lag and insertion loss drift while maintaining high linearity and isolation over an extended frequency range up to 40 GHz.

	Product Description[1]	Part Number	Operating Frequency (MHz)		Linearity IIP3/IIP2 (dBm)	P0.1dB (dBm)	Insertion Loss (dB)		Isolation (dB)		Settling Time (µs)[2]	Switching Time (µs)[3]	ESD HBM (V)	Package
			Min	Max			Min	Max	Min	Max				
	SPDT, A	PE42520	0.009	13000	66 / 120	39	0.6	2.0	18	90	15	5.5	4000	16L 3×3 QFN
	SPDT, A	PE42521	0.009	13000	65 / 120	38	0.6	1.85	17	90	2	0.5	3000	16L 3×3 QFN
NEW	SPDT, A	PE42522	0.009	26500	59 / 121	33	0.7	5.3	22	73	7	3	3500	29L 4×4 LGA
NEW	SPDT, A	PE42523	0.009	26500	59 / 125	33	0.75	5.7	22	75	2	0.5	2500	29L 4×4 LGA
NEW	SPDT, A	PE42553	0.009	8000	66 / 120	39	0.6	0.85	41	90	15	5.5	4000	16L 3×3 QFN
NEW	SPDT, R	PE42524	10	40000	50 / –	32.5	0.6	5.5	33	84	0.84	0.225	2000	Flip Chip
	SPDT, R	PE42551	0.009	6000	50 / –	34	0.55	0.9	21	29	–	7	500	20L 4×4 QFN
	SP4T, A	PE42540	.00001	8000	58 / 100	33	0.7	1.2	31	84	15	5	2000	32L 5×5 LGA
NEW	SP4T, A	PE42542	0.009	18000	58 / 118	33	0.7	3.1	27	90	7	3	3500	29L 4×4 LGA
NEW	SP4T, A	PE42543	0.009	18000	59 / 113	33	0.7	3.2	29	90	2	0.5	2500	29L 4×4 LGA

Note 1: Absorptive (A) or Reflective (R).
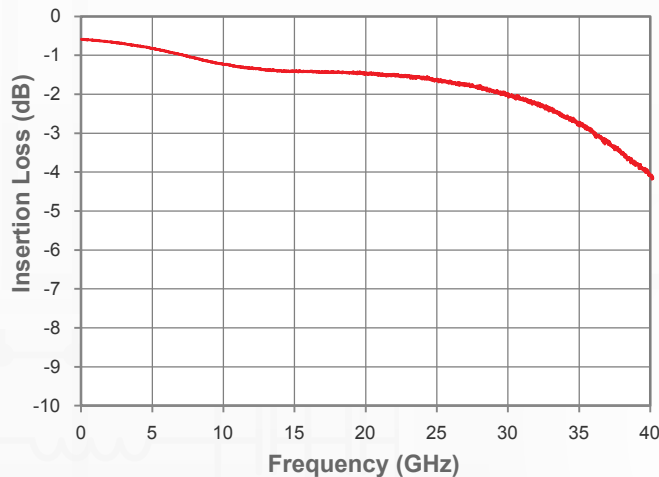**Note 2:** 50% CTRL to 0.05 dB final value.

Note 3: 50% CTRL to 90% or 10% RF.

High-frequency Examples: Breakthrough RF Performance

UltraCMOS high-frequency switches provide best-in-class, stable and consistent performance across the entire frequency range.
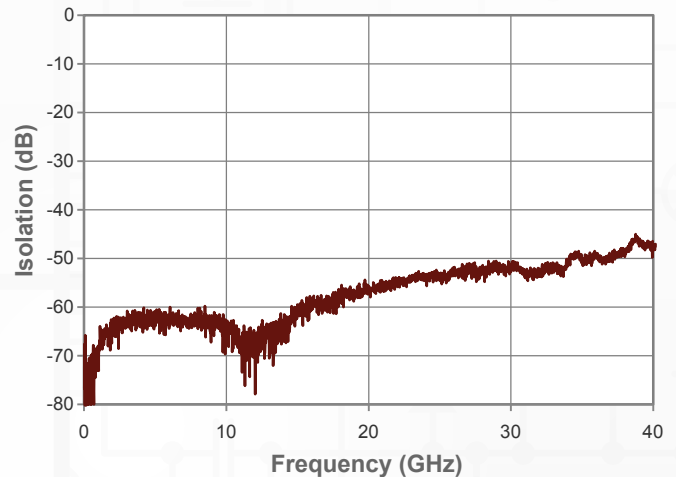
PE42524 Insertion Loss

Predictable and smooth insertion loss behavior over a broad frequency range.

PE42524 Isolation

Ground-breaking port-to-port isolation of 50 dB at 35 GHz.

Note: For additional information about optimizing high-frequency performance, please see application note AN42.

True DC RF Switch

Peregrine's new UltraCMOS PE42020 is the industry's first and only RF integrated switch to operate at zero Hz. This True DC RF switch features high power handling and maintains excellent RF performance and linearity from DC through 8000 MHz.
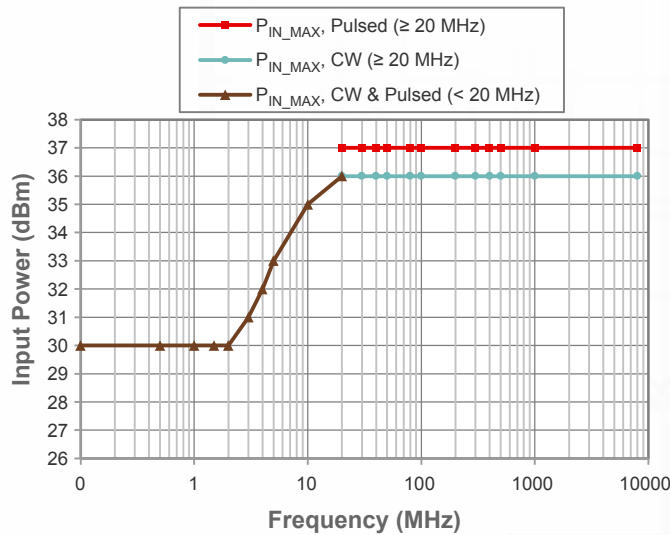
True DC RF Switch — 50Ω												
Product Description	Part Number	Operating Frequency		Linearity IIP3/IIP2 (dBm)	P0.1dB (dBm)	Insertion Loss (dB)		Isolation (dB)		Settling Time (µs)[2]	Switching Time (µs)[3]	ESD HBM (V)	Package
		Min	Max			Min	Max	Min	Max				
NEW SPDT, A & R[1]	PE42020	0 Hz	8000 MHz	62 / 115	38	0.6	1.1	34	48	35	10	1000	20L 4×4 QFN

Note 1: Configurable 50Ω Absorptive (A) or open Reflective (R) switch. **Note 3:** 50% CTRL to 90% or 10% RF.
Note 2: 50% CTRL to 0.05 dB final value.

PE42020 Power Handling

The PE42020 exhibits high power handling of 30 dBm at 0 Hz and 36 dBm at 8 GHz. This graph shows the maximum RF input power (P_{IN_MAX}) for pulsed, CW and CW/pulsed at 0 °C to +85 °C ambient temperature, V_{DD} = +15V, and V_{SS} = −15V.

High-power RF Switches

UltraCMOS high-power switches change the paradigm of high-power switch design by providing a solution that delivers a cost-effective, simple to design-in long-term solution—a small footprint, monolithic, turnkey design with extremely low power consumption, excellent harmonic performance and high power handling.

High-power RF Switches — 50Ω										
Product Description*	Part Number	Operating Frequency (MHz)		P0.1dB (dBm)	Insertion Loss (dB)		Isolation (dB)		Harmonics 2fo/3fo (dBc)	ESD HBM (V)	Package
		Min	Max		Min	Max	Min	Max			
SPDT, R	PE42820	30	2700	45.5	0.3	0.7	24	35	−94 / −84	1500	32L 5×5 QFN
SPDT, R	PE42821	100	2700	45.5	0.4	0.8	24	35	−82 / −85	1500	32L 5×5 QFN
SP3T/SP5T, R	PE42850	30	1000	45.5	0.25	0.35	30	36	−90 / −90	1500	32L 5×5 QFN
SP3T/SP5T, R	PE42851	100	1000	45.5	0.25	0.4	30	36	−80 / −80	1500	32L 5×5 QFN

Note: * Reflective (R).

Automotive AEC-Q100 Certified Switches

Peregrine's automotive RF switches are AEC-Q100 Grade 2 certified and capable of supporting operating temperatures up to +105 °C.

AEC-Q100
Certified

Automotive AEC-Q100 Certified Switches

Product Description*	Part Number	Operating Frequency (MHz)		Linearity IIP3/IIP2 (dBm)	P0.1dB (dBm)	Insertion Loss (dB)		Isolation (dB)		Typical I_{DD} (µA @ 3V)	V_{DD} Range (V)	ESD HBM (V)	Package
		Min	Max			Min	Max	Min	Max				
NEW SPDT, R	PE423422	100	6000	73.5 / 115	34	0.25	0.9	16	41	120	2.3–5.5	1000	12L 2×2 QFN
SPDT, R	PE42359	10	3000	55 / –	33.5	0.35	1.1	14	35	9	1.8–3.3	2000	6L SC70
SP4T, R	PE423641	50	3000	68 / 115	37	0.5	0.95	22	32	13	2.65–3.3	2000	16L 3×3 QFN

Note: * Reflective (R).

Wired Broadband 75Ω Switches

Simplify your next RF design with high-performance UltraCMOS 75Ω switches. Excellent isolation, low insertion loss and a CMOS / TTL compatible control allow Peregrine RF switches to address the needs of most wired broadband applications.

Wired Broadband Switches — 75Ω

Product Description[1]	Part Number	Product Highlight	Operating Frequency (MHz)		CTB / CSO (dBc)	P0.1dB (dBm)	Insertion Loss (dB)		Isolation (dB)		V_{DD} Range (V)	ESD HBM (V)	Package
			Min	Max			Min	Max	Min	Max			
SPST, A	PE4270	Low Insertion Loss	1	3000	−90[2]	30	0.5	0.7	63	90	2.7–3.3	500	6L 3×3 DFN
SPDT, A	PE4256	Low Insertion Loss	5	3000	−90[2]	31	0.5	1.1	52	80	2.7–3.3	1000	20L 4×4 QFN
SPDT, A	PE4280	High Isolation	5	2200	−85[2]	26	0.5	1.1	47	72	2.7–3.3	1000	20L 4×4 QFN
SPDT, A	PE42720	High Isolation	5	3000	−104[3]	31	0.6	1.0	60	70	2.7–5.5	2500	20L 4×4 LGA
SPDT, A	PE42721	Low Insertion Loss	5	2200	−99 / <−105	27	0.4	0.65	53	85	2.3–5.5	3000	12L 3×3 QFN
NEW SPDT, R	PE42722	High Linearity, DOCSIS 3.1	5	1794	Note 4	Note 5	0.2	0.85	29	50	2.3–5.5	1500	32L 5×5 QFN

Note 1: Absorptive (A) or Reflective (R).
Note 2: CTB / CSO measured with 77 and 110 channels; PO = 44 dBmV.
Note 3: CTB / CSO measured with 159 channels; PO = 42 dBmV.
Note 4: This product is specified for DOCSIS 3.1. See datasheet for harmonics specs.
Note 5: P0.1dB = 88 dBmV.

Wired Broadband Switches — 75Ω — With Unpowered Operation

Product Description[1]	Part Number	Operating Frequency (MHz)		CTB / CSO (dBc)	P1dB[2] pwr / unpwr (dBm)	Insertion Loss pwr (dB)		Isolation pwr / unpwr (dB)		V_{DD} Range (V)	ESD HBM (V)	Package
		Min	Max			Min	Max	Min	Max			
SPDT, A	PE42742	5	2200	−90 / −77[3]	32 / 26.5	0.45	1.7	53 / 52.5	94 / 90.5	2.7–3.3	3500	20L 4×4 QFN
SPDT, A	PE42750	5	2200	−81 / −110[4]	23.5	0.7	1.7	57 / 72	84 / 90	2.7–3.6	2000	12L 3×3 QFN

Note 1: Absorptive (A).
Note 2: Measured at 1 GHz.
Note 3: CTB / CSO measured with 77 and 110 channels; PO = 44 dBmV.
Note 4: CTB / CSO measured with 159 channels; PO = 42 dBmV.

75Ω
50Ω

*Our general-purpose reflective 50Ω switches can also be used in a 75Ω environment.*

Monolithic Phase and Amplitude Controller (MPAC)

Designed for the LTE and LTE-A wireless-infrastructure transceiver market, the UltraCMOS MPAC device is ideally suited to enhance system performance, lower bill of material (BOM) costs, increase reliability and provide maximum tuning flexibility for Doherty amplifier architectures found in wireless infrastructure applications.

Monolithic Phase and Amplitude Controller (MPAC) — 50Ω												
Product Description, Part Number	Phase (°) (range / steps) 5 bits	Attenuation (dB) (range / steps) 4 bits	Programming Mode	Operating Frequency (GHz)		Insertion Loss (dB)	Input IP3 (dBm)	P0.1dB (dBm)	V_{DD} Range (V)	I_{DD} (µA)	ESD HBM (V)	Package
				Min	Max							
NEW 5/4-bit – PE46120	−87.2 / 2.8	7.5 / 0.5	Serial	1.8	2.2	6.9	60	35	2.3–5.5	350	1000	32L 6×6 QFN

Relative Phase RF$_{IN}$ to RF$_{OUT}$ (All Phase States)

MPAC
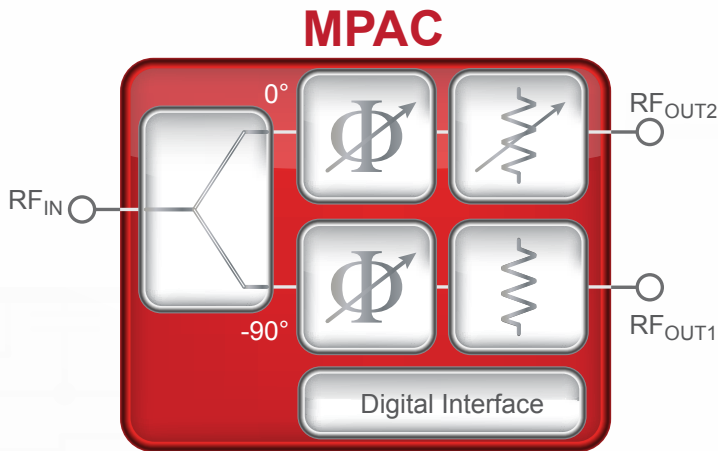
The PE46120 is highly monotonic over a broad frequency range for all RF$_{OUT1}$/RF$_{OUT2}$ phase states.

Relative Phase RF$_{IN}$ to RF$_{OUT2}$

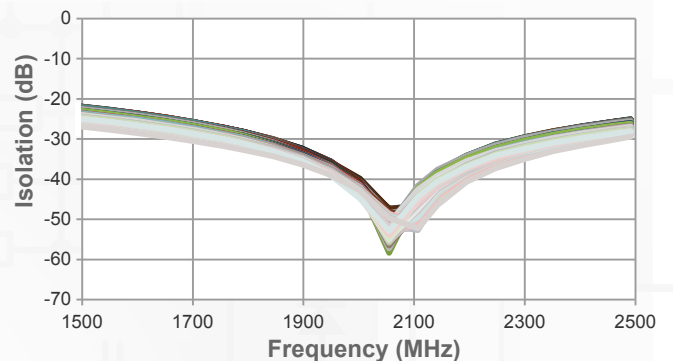Relative Phase RF$_{IN}$ to RF$_{OUT1}$
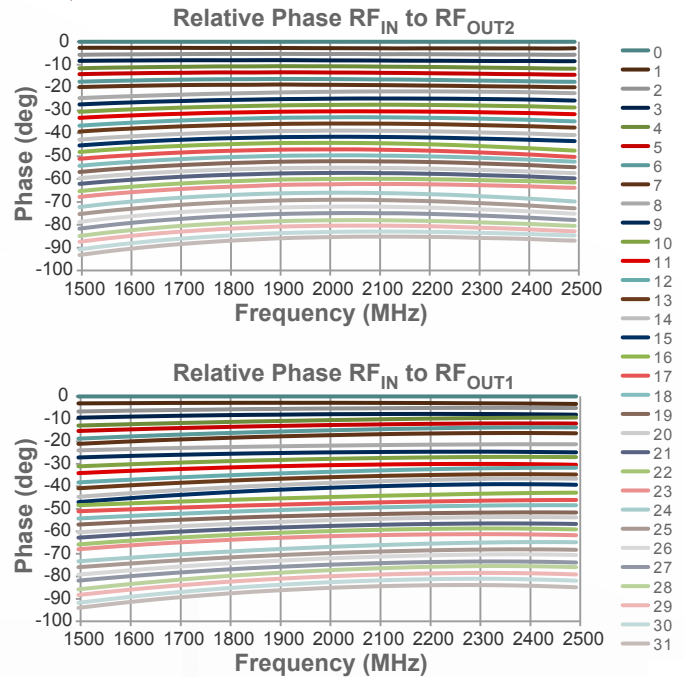
Phase Variation Across Atten State

Excellent phase stability across all RF$_{OUT}$ attenuation states.
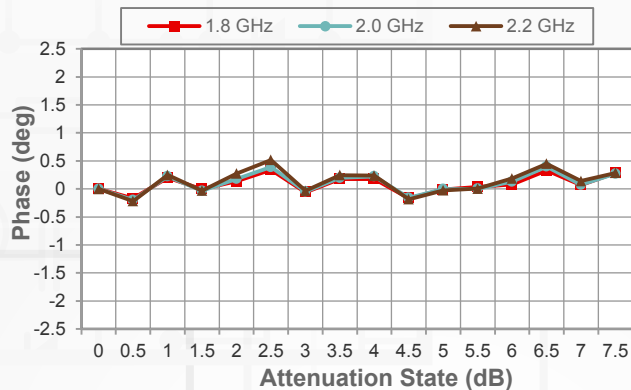
Isolation Output Ports (All States)

High isolation across all phase and attenuation states.

Glitch-less Digital Step Attenuators (DSAs)

Peregrine's new glitch-less DSAs feature a novel architecture to provide the best-in-class glitch-less transition behavior when changing attenuation states and is specified to support temperatures all the way up to 105 ˚C.

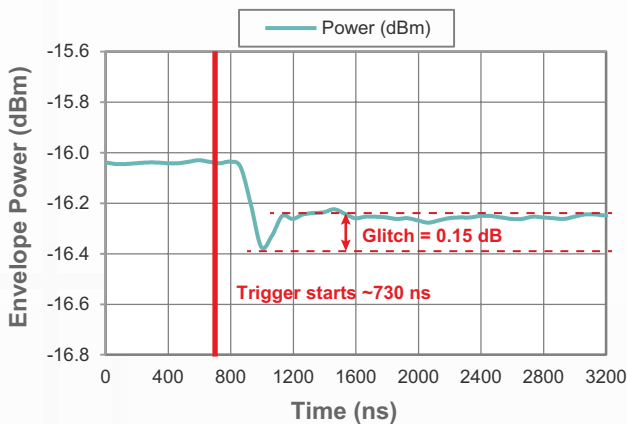| Glitch-less Digital Step Attenuators (Monolithic) — 50Ω											
Product Description, Part Number	Attenuation (dB) (range / steps)	Programming Mode	Operating Frequency (MHz)		Insertion Loss (dB)		Input IP3 (dBm)	Attenuation Accuracy (dB @ 2.2 GHz)	Switching Speed (µs)	ESD HBM (V)	Package
			Min	Max	Min	Max					
NEW 7-bit – PE43711	31.75 / 0.25, 0.5, 1.0	Parallel[2], Serial	0.009	6000	1.3	2.4	57	±(0.15 + 1.5% of setting)	0.275	3000	24L 4×4 QFN
NEW 7-bit – PE43712	31.75 / 0.25, 0.5, 1.0	Parallel[2], Ser-Add.[3]	0.009	6000	1.3	2.45	57	±(0.20 + 1.5% of setting)	0.275	3000	32L 5×5 QFN
NEW 7-bit – PE43713[1]	31.75 / 0.25, 0.5, 1.0	Parallel[2], Ser-Add.[3]	0.009	6000	1.3	2.45	57	±(0.20 + 1.5% of setting)	0.275	3000	32L 5×5 QFN

Note 1: External V_{SS} option.   **Note 2:** Parallel Modes: Latched and Direct.   **Note 3:** Serial-Addressable Mode.
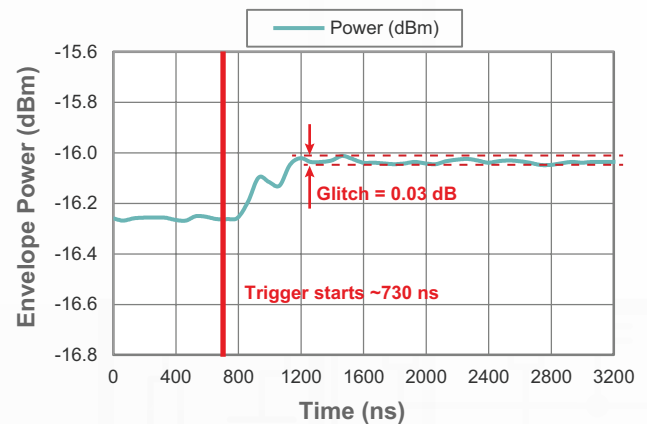
Glitch-less Attenuation Transient: 15.75 to 16 dB

Typical Switching Time = 275 ns

Glitch-less Attenuation Transient: 16 to 15.75 dB

Typical Switching Time = 275 ns

50Ω and 75Ω Digital Step Attenuators (DSAs)

Digital Step Attenuators (Monolithic) — 50Ω											
Product Description, Part Number	Attenuation (dB) (range / steps)	Programming Mode	Operating Frequency (MHz)		Insertion Loss (dB)		Input IP3 (dBm)	Attenuation Accuracy (dB @ 1 GHz)	Switching Speed (µs)	ESD HBM (V)	Package
			Min	Max	Min	Max					
2-bit – PE43205[1]	18 / 6, 12	Parallel	35	6000	0.5	1.05	61	+0.10	0.029	2000	12L 3×3 QFN
NEW 6-bit – PE4312[1]	31.5 / 0.5	Parallel[2], Serial	1	4000	1.3	2.1	59	±(0.15 + 2% of setting)	0.6	2000	20L 4×4 QFN
7-bit – PE43704	31.75 / 0.25, 0.5, 1.0	Par[2], Ser, Ser-Add.[3]	0.009	8000	1.3	2.4	61	+(0.15 + 3% of setting) −(0.1 + 1% of setting)	1.1	1500	32L 5×5 QFN
7-bit – PE43705[1]	31.75 / 0.25, 0.5, 1.0	Par[2], Ser, Ser-Add.[3]	50	8000	1.3	2.4	65	+(0.15 + 1.5% of setting) −(0.1 + 1% of setting)	1	1500	32L 5×5 QFN

Note 1: Operating temperature up to +105 °C.   **Note 2:** Parallel Modes: Latched and Direct.   **Note 3:** Serial-Addressable Mode.

Broadband Digital Step Attenuators (Monolithic) — 75Ω										
Product Description, Part Number	Attenuation (dB) (range / steps)	Programming Mode	Operating Frequency (MHz)		Insertion Loss (dB)	Input IP3 (dBm)	Attenuation Accuracy (dB @ 1 GHz)	Switching Speed (µs)	ESD HBM (V)	Package
			Min	Max						
4-bit – PE43404	15 / 1.0	Parallel*, Serial	1	2000	1.4	52	±(0.25 + 7% of setting)	1	500	20L 4×4 QFN
5-bit – PE4307	15.5 / 0.5	Parallel*, Serial	1	2000	1.4	52	±(0.15 + 4% of setting)	1	500	20L 4×4 QFN
5-bit – PE4308	31 / 1.0	Parallel*, Serial	1	2000	1.4	52	±(0.20 + 4% of setting)	1	500	20L 4×4 QFN
6-bit – PE4304	31.5 / 0.5	Parallel*, Serial	1	2000	1.4	52	±(0.15 + 4% of setting)	1	500	20L 4×4 QFN

Note: * Parallel Modes: Latched and Direct.

Digital Phase Shifters

Get flexibility for the most design stringent requirements with high linearity, excellent harmonic performance, extended phase range, high resolution, low RMS phase and amplitude error and dual programming options.

Digital Phase Shifters (Monolithic) — 50Ω											
Part Number	Operating Frequency (GHz)	Bit #	Range (°)	Resolution (°)	Insertion Loss (dB)	RMS Phase Error (°)	RMS Amplitude Error (dB)	Settling Time (ns)	V_{DD} Range (V)	ESD HBM (V)	Package
NEW PE44820[1]	1.7–2.2	8	358.6	1.4	6	1.05	0.15	355	2.3–5.5	1000	32L 5×5 QFN

Note: * Operating temperature up to +105 °C.

Power Limiting Devices

Peregrine's power limiters represent the industry's first turnkey, monolithic solutions to provide an alternative to discrete, PIN-diode limiters based on gallium arsenide (GaAs). UltraCMOS power limiters deliver simple, repeatable and reliable protection, ideal for test-and-measurement, land mobile radio (LMR), wireless-infrastructure, military and radar systems.
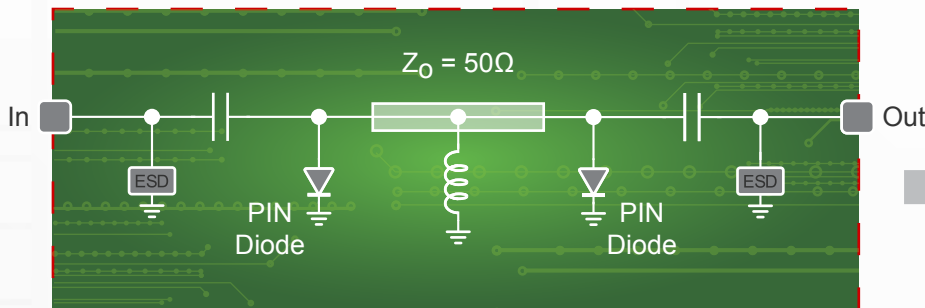
Power Limiters								
Part Number	Operation Modes	Operating Frequency	Adjustable Power Limiting Threshold (dBm)	Max Power Handling (dBm)		Input IP3 (dBm)	Control Voltage Range (V)*	ESD HBM (V)	Package
				Pulsed (50W)	CW (10W)				
NEW PE45140	Limiting, Reflecting	20–2000 MHz	22–32	47	40	64	–2.5 to –0.5	8000	12L 3×3 QFN
NEW PE45450	Limiting, Reflecting	9 kHz–6 GHz	25–35	47	40	70	–2.5 to –0.5	8000	12L 3×3 QFN

Note: * Limiting Mode.

Replacing GaAs Solutions

An UltraCMOS power limiting device is up to eight times smaller than traditional GaAs solutions and offers better linearity, versatility and reliability.

8x smaller while maintaining the same power dissipation

UltraCMOS® RFICs deliver extraordinary ESD tolerance — up to 8 kV HBM in the new power limiting devices.

Phase-locked Loop (PLL) Frequency Synthesizers

Peregrine's Integer-N PLLs are ideal for base station systems — local multiband distribution service (LMDS), multichannel multiband distribution service (MMDS), wireless local loop (WLL) — as well as RF frequency generation; L-, S- and C-band synthesizers; and clock recovery in communication systems, mobile terminals, telemetry, radar and portable radios.

Integer-N Phase-locked Loop (PLL) Frequency Synthesizers										
Part Number	Φ Det Type	Programming Mode	Max Input Operating Freq			Prescaler	Main Counters M, A	Reference Counters	Typical Idd (mA @ 2.8V)	ESD HBM (V)	Package
			(GHz) RF PLL	(MHz) Ref	(MHz) Compare						
NEW PE33241[1]	PD	Serial, Hardwire	4 (5/6 bit) 5 (10/11 bit)	100 (prescaler) 800 (bypass)	100	5/6, 10/11, bypass	9-bit, 4-bit	6-bit	75	1000	48L 7×7 QFN
PE83336[2,3]	PD	Parallel, Serial, Hardwire	3	100	20	10/11	9-bit, 4-bit	6-bit	20	1000	44L CQFJ

Note 1: V_{DD} range = 2.65–2.95V. **Note 3:** Not available for Space Level Screening.
Note 2: V_{DD} range = 2.85–3.15V.

Mixers

Peregrine's UltraCMOS mixers are broadband, quad MOSFET (metal-oxide-semiconductor field-effect transistor) array cores. The integrated receive mixers feature high linearity, strong low-frequency performance, monolithic integration and high reliability, making them easier to implement and more dependable than gallium arsenide (GaAs)-based MOSFET arrays.

Mixer Core[1]										
Part Number	Operating Frequency (MHz)			LO Drive (dBm)	Conv Loss (dB)	Isolation (dB, typ)		Input IP3 (dBm, typ)	ESD HBM (V)	Package
	LO	RF	IF, Nom			LO-RF	LO-IF			
PE4140[2]	0.01–6000	0.01–6000	0.01–6000	0–20	6.5–7.5	25–40	25–40	36	100	6L 3×3 DFN, DIE
PE4141[2]	0.01–1000	0.01–1000	0.01–1000	0–20	7.0–8.0	40	40	33	100	8L MSOP

Note 1: Fully differential DC coupled ports. External baluns required. **Note 2:** MOSFET Quad Array.

High-reliability Products

Peregrine Semiconductor's UltraCMOS silicon on sapphire (SOS), a patented variation of silicon-on-insulator (SOI) technology, has achieved significant performance milestones in reliability and RF performance, making them well suited for demanding High-reliability (Hi-Rel) designs. UltraCMOS products are designed to meet stringent low-power requirements of telecom, infrastructure, microwave and VSAT military radios, radar and ECM space systems and test instrumentation applications. All Hi-Rel devices are available in ceramic hermetic packaging and in die form. Screening is available for commercial space designs.

Scan the QR code to learn more about Peregrine's High-reliability products.

Digital Tuning Solutions

In complex radio designs where detuning can cause increased filter loss, power amplifier (PA) inefficiencies and antenna mismatch, signal-chain performance can be significantly improved with a monolithically integrated solid-state impedance tuning solution. Peregrine's digitally tunable capacitor (DTC) and tunable control switch products continue a tradition of innovation, high performance and ease-of-use by offering tunability, high-voltage handling and excellent linearity.

Digitally Tunable Capacitors

| Part Number | Interface | Operating Frequency (MHz) | | Min Shunt Capacitance (pF) | Max Shunt Capacitance (pF) | Tuning Ratio (Shunt) | Quality Factor (Shunt, 1 GHz) | | Peak Operating Voltage (V_{PK}) | V_{DD} Range (V) | ESD HBM (V) | Package |
		Min	Max				Cmin	Cmax				
PE64101	SPI	100	3000	1.38	5.90	4.3:1	50	20	6	2.3–3.6	2000	12L 2×2 QFN
PE64102	SPI	100	3000	1.88	14	7.4:1	50	20	6	2.3–3.6	2000	12L 2×2 QFN
PE64904	SPI	100	3000	1.10	5.10	4.6:1	35	25	30	2.3–3.6	1500	10L 2×2 QFN
PE64905	I²C	100	3000	1.10	5.10	4.6:1	35	25	30	2.3–3.6	1500	10L 2×2 QFN
PE64906	SPI	100	3000	0.90	4.60	5.1:1	40	19	30	2.3–4.8	2000	10L 2×2 QFN
PE64907	SPI	100	3000	0.85	2.40	2.82:1	40	34	30	2.3–4.8	2000	10L 2×2 QFN
PE64908	SPI	100	3000	2.15	7.70	3.6:1	40	13	30	2.3–4.8	2000	10L 2×2 QFN
PE64909	SPI	100	3000	0.60	2.35	3.9:1	40	27	30	2.3–4.8	2000	10L 2×2 QFN

Tuning Control Switches

| Product Description*	Part Number	Operating Frequency (MHz)		Interface	R_{ON} (Ω)	C_{OFF} (pF)	V_{DD} Range (V)	ESD HBM (V)	Package
SPST	PE613010	100	3000	GPIO	1.2	0.40	2.3–5.5	2000	10L 2×2 QFN
SP4T	PE613050	100	3000	GPIO	1.6	0.14	2.3–5.5	2000	12L 2×2 QFN

Note: * Open reflective switches.

Antenna Impedance Tuning

The DTC tuner increases power delivered to the antenna by eliminating mismatch loss.

Power Delivered to Antenna
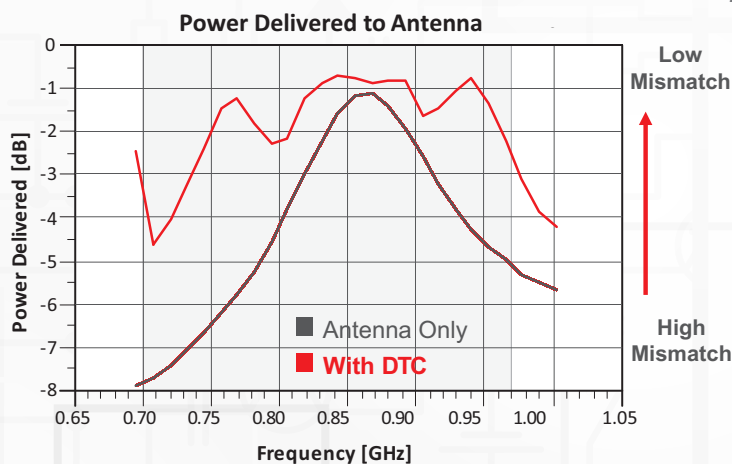
Tunable Matching Networks

Match the desired impedance to 50Ω or other impedance over broadband (700–2200 MHz) to minimize mismatch loss.
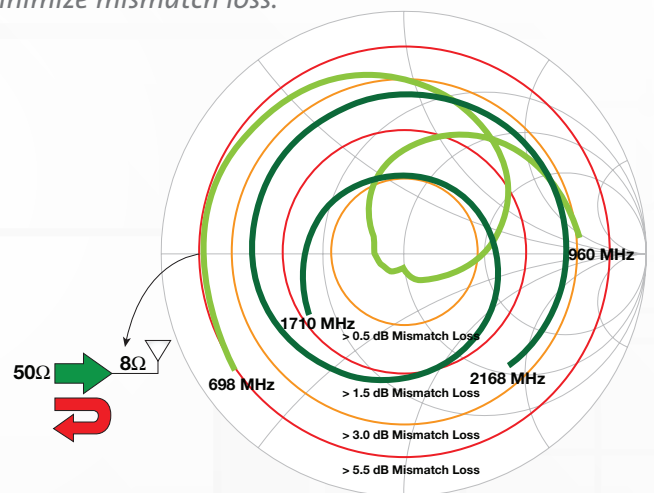
Quality and
Reliability

We are committed to providing high-quality products and services that meet or exceed our customers' expectations. We have developed and implemented a quality management system to create an organizational environment designed to meet the highest level of quality and reliability standards. Our quality manag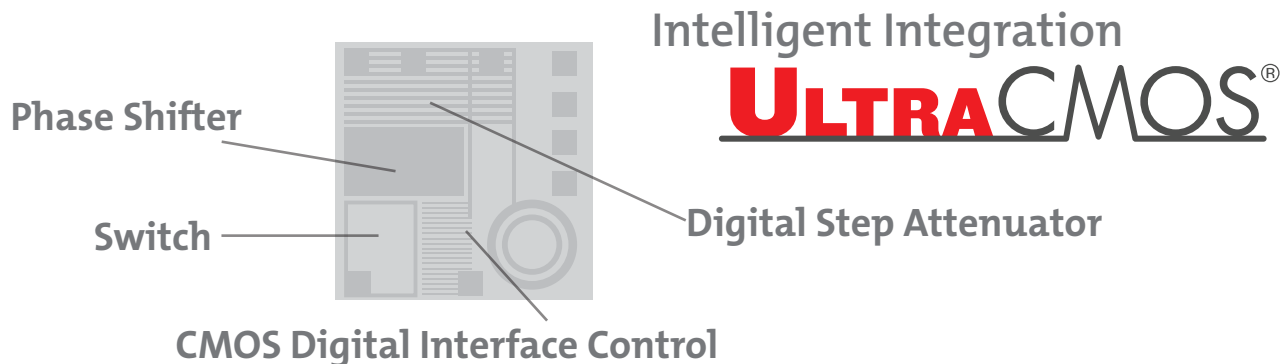ement system has been certified and maintained to ISO 9001 standards since 2001. We achieved AS9100 Quality Management System Standards certification in 2003 to address the strict quality system requirements of the aerospace industry. In early 2012, we further improved the robustness of our quality management system by receiving our ISO/TS 16949:2009 Quality Management System certification by the automotive industry.
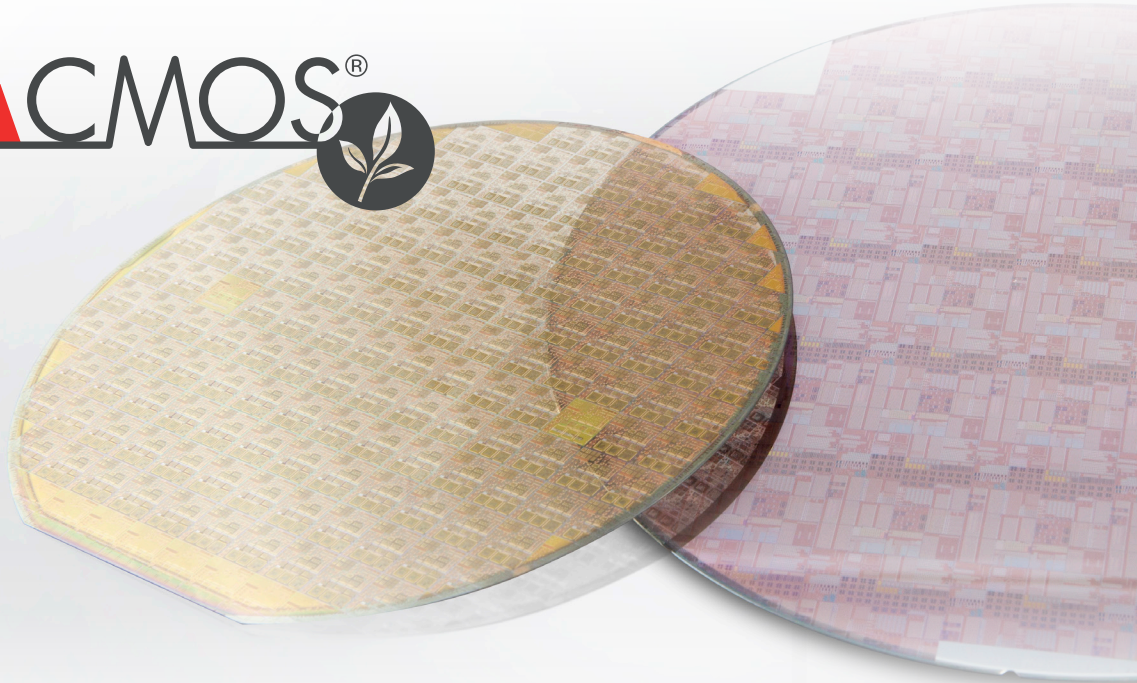
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Coming Soon

As the world's leading RF SOI company, Peregrine is committed to providing new product lines that meet the exacting requirements in a broad range of applications in aerospace and defense, broadband, industrial, mobile wireless device, test-and-measurement (T&M) equipment and wireless-infrastructure markets. Watch for some of our upcoming products.

Core Chip This X-band device will revolutionize Synthetic Aperture Radar. A single chip that uses monolithic microwave integrated circuit (MMIC) design techniques controlled through a standard digital interface, this product delivers the fine resolution and degree of control critical for radar applications.

Intelligent Integration

ULTRACMOS®

Phase Shifter

Switch

Digital Step Attenuator

CMOS Digital Interface Control

ULTRA CMOS® GREEN

Going Green Starts on the Inside

The UltraCMOS process, a high-performance variation of SOI, is not based on arsenic (as are all GaAs-based devices) but instead incorporates a sapphire or silicon substrate, which intrinsically offers both environmental as well as RF benefits. See Peregrine's Green Package Information sheet and Certificate of Conformance on psemi.com to learn more.

RoHS-compliant Commercial Packaging Options

6L SC70
1.3 × 2.0 × 1.0

8L 1.5×1.5 DFN
1.5 × 1.5 × 0.50

10L 2×2 QFN
2.0 × 2.0 × 0.45

12L 2×2 QFN
2.0 × 2.0 × 0.60

8L MSOP
3.0 × 3.0 × 1.1

6L DFN
3.0 × 3.0 × 0.9

12L 3×3 QFN
3.0 × 3.0 × 0.75

16L 3×3 QFN
3.0 × 3.0 × 0.75

20L 4×4 LGA
4.0 × 4.0 × 0.9

20L 4×4 QFN
4.0 × 4.0 × 0.9

24L 4×4 QFN
4.0 × 4.0 × 0.9

24L 4×4 LGA
4.0 × 4.0 × 0.9

29L 4×4 LGA
4.0 × 4.0 × 0.9

32L 5×5 QFN
5.0 × 5.0 × 0.9

32L 5×5 LGA
5.0 × 5.0 × 0.9

32L 6×6 QFN
6.0 × 6.0 × 0.9

48L 7×7 QFN
7.0 × 7.0 × 0.9

All dimensions are listed in millimeters (width × length × height) and are approximate.
See product datasheets for exact dimensions.

Design and
Application Support

Designing for tomorrow's challenging RF applications requires high-performance products and outstanding technical support. From our engineering excellence to streamlined manufacturing and technical sales and applications support, Peregrine Semiconductor is committed to providing a complete product solution. Choose among our comprehensive library of datasheets, application notes, tutorials, reference designs and other engineering resources, all developed to help get your design to market on time.

Online Support System – support.psemi.com

Visit our website to find the technical resources you need.

Sales Offices

The Americas
Peregrine Semiconductor
Corporation
9380 Carroll Park Drive
San Diego, CA USA 92121
Phone: +1.858.731.9400
Fax: +1.858.731.9499
E-mail: Sales@psemi.com

Europe
Peregrine Semiconductor, Europe
Merlin House, Brunel Way,
Theale, Berkshire
RG7 4AB
United Kingdom
Phone: +44.118.902.6520
E-mail: Sales@psemi.com

Asia Pacific
Peregrine Semiconductor, China
Room 811, Building 3
Lane 58 East Xinjian Road
Shanghai, China 201199
Phone: +86.21.5836.8276
Fax: +86.21.5836.8550
E-mail:
   Sales_NorthChina@psemi.com
   Sales_SouthChina@psemi.com

Peregrine Semiconductor, Korea
#C-3004, Kolon Tripolis, 210
Geumgok-dong, Bundang-gu,
Seongnam-si Gyeonggi-do,
463-943 South Korea
Phone: +82.31.728.3939
Fax: +82.31.728.3940
E-mail: Sales_Korea@psemi.com

Peregrine Semiconductor, Taiwan
Phone: +886.970164578
Fax: +886.2.2822.5867
E-mail: Sales_Taiwan@psemi.com

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